



## N-Channel 60-V (D-S) MOSFET

### PRODUCT SUMMARY

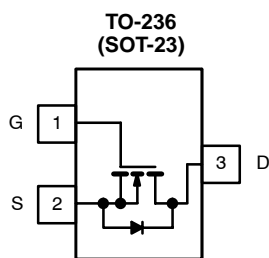
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.16 @ $V_{GS} = 10$ V	2.0
	0.22 @ $V_{GS} = 4.5$ V	1.7

### FEATURES

- 100%  $R_g$  Tested
- RoHS Compliant



Pb-free  
Available



Top View  
Si2308DS (A8)\*

\*Marking Code

Ordering Information: Si2308DS-T1  
Si2308DS-T1—E3 (Lead (Pb)-Free)

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	2.0	A
		1.6	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	10	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	1.0	
Maximum Power Dissipation <sup>a</sup>	$P_D$	1.25	W
		0.80	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>c</sup>		166	

#### Notes

- Surface Mounted on FR4 Board,  $t = \leq 5$  sec.
- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>

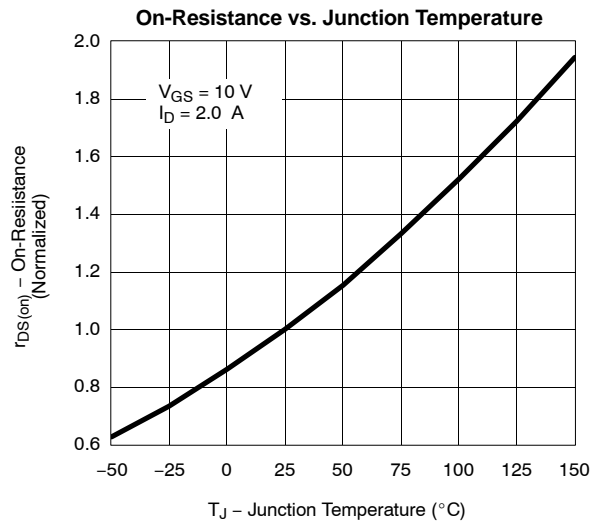
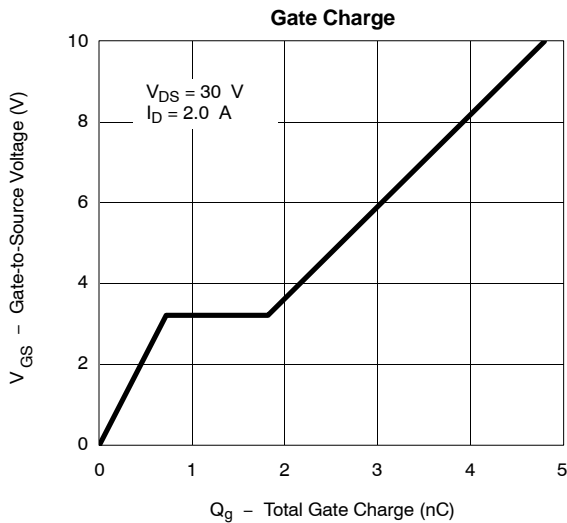
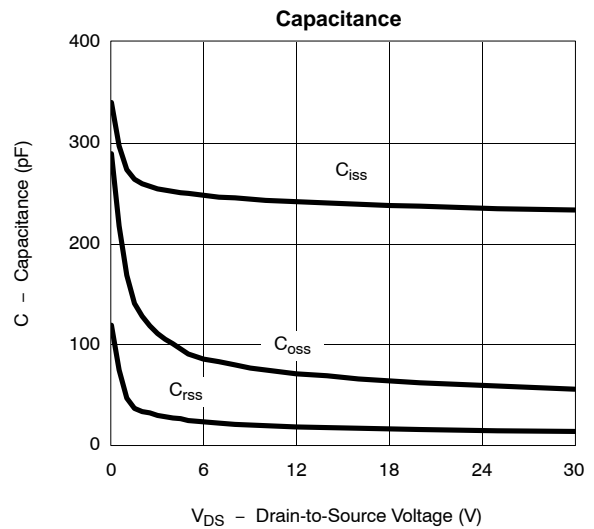
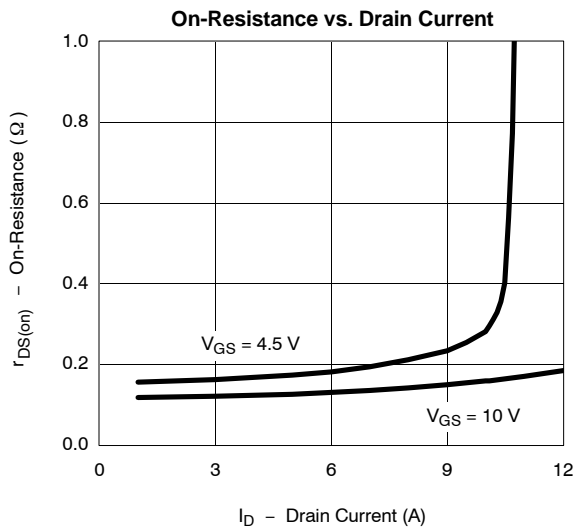
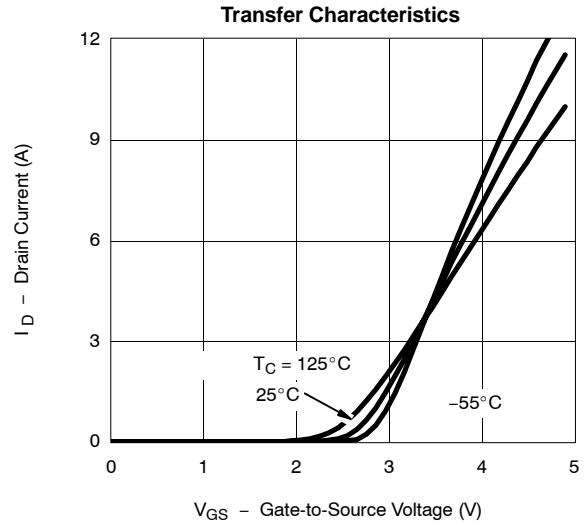
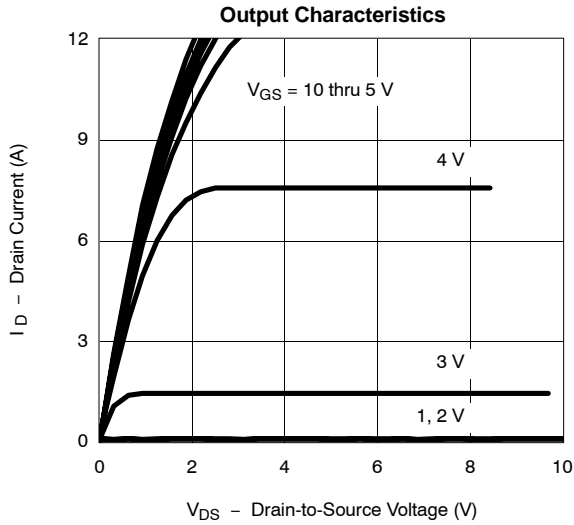
SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5		3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			0.5	μA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 4.5 V, V <sub>GS</sub> = 10 V	6			A
		V <sub>DS</sub> ≥ 4.5 V, V <sub>GS</sub> = 4.5 V	4			
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A		0.125	0.16	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1.7 A		0.155	0.22	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 4.5 V, I <sub>D</sub> = 2.0 A		4.6		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		0.77	1.2	V
Dynamic						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.0 A		4.8	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.8		
Gate-Drain Charge	Q <sub>gd</sub>			1.0		
Gate Resistance	R <sub>g</sub>		0.5		3.3	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		240		pF
Output Capacitance	C <sub>oss</sub>			50		
Reverse Transfer Capacitance	C <sub>rss</sub>			15		
Switching						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 30 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 6 Ω		7	15	ns
Rise Time	t <sub>r</sub>			10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>			17	35	
Fall Time	t <sub>f</sub>			6	15	

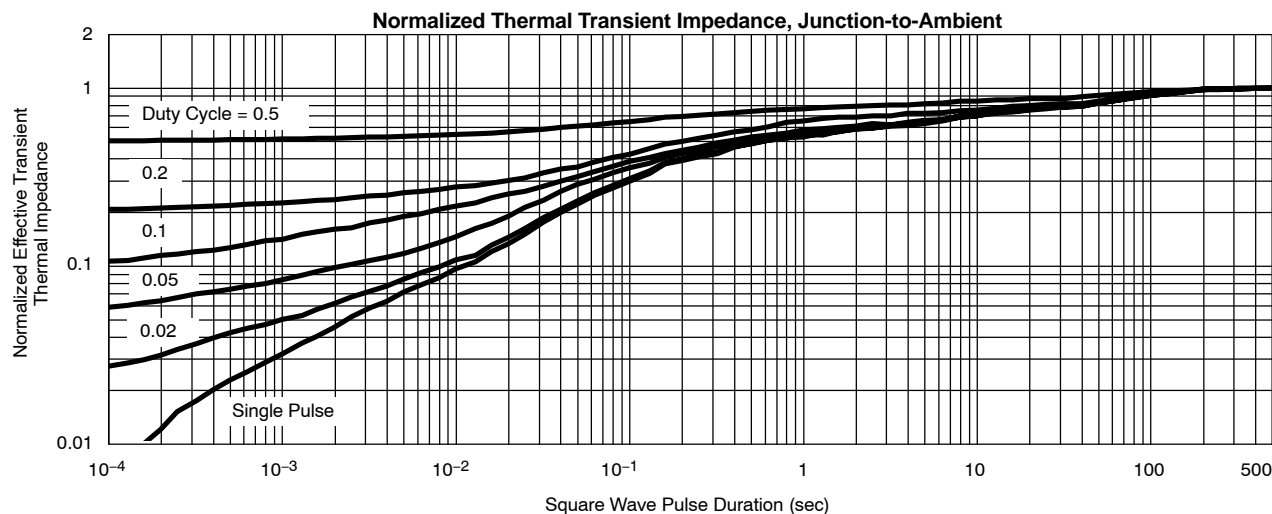
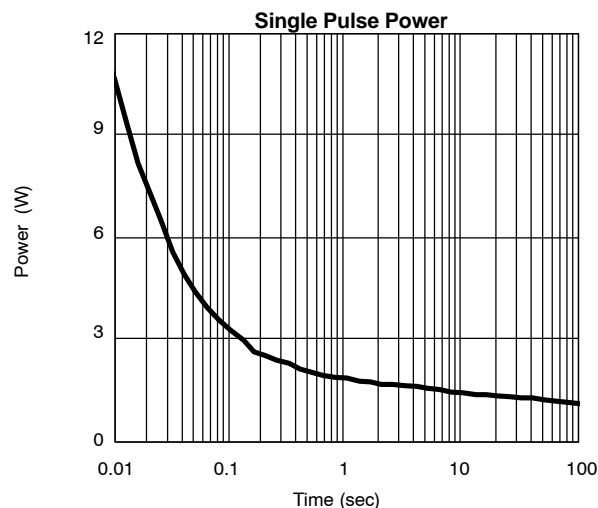
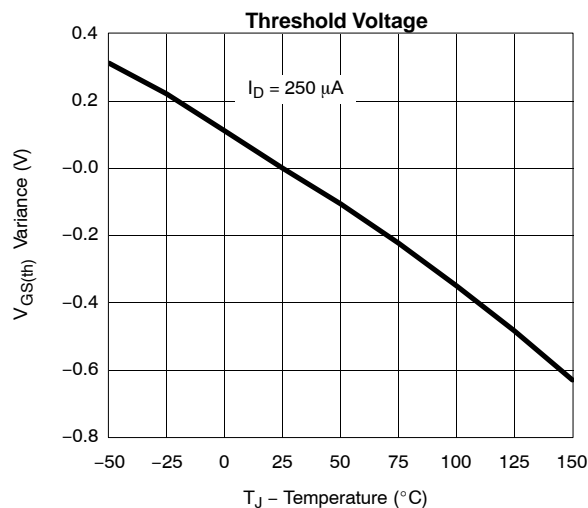
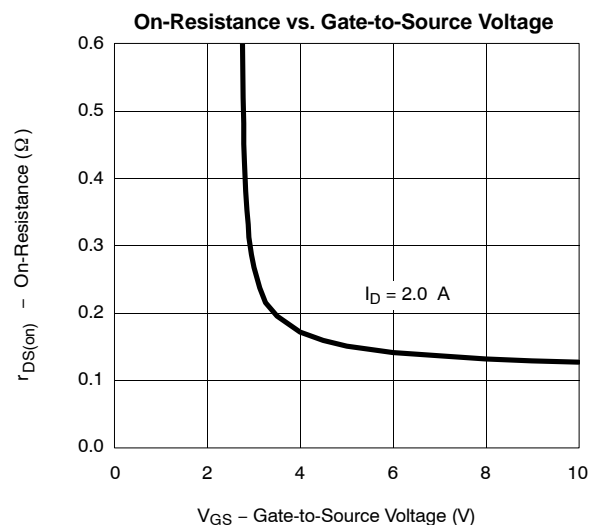
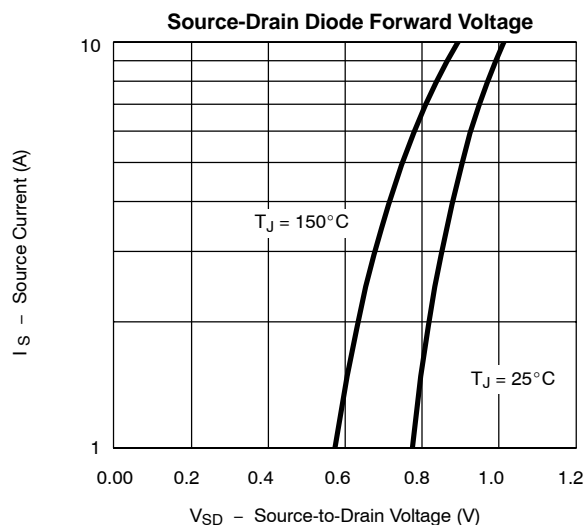
## Notes

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**


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